



#### N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	3.2mΩ @ V <sub>GS</sub> = 10V	100A
30V	5.2mΩ @ V <sub>GS</sub> = 4.5V	80A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

# **Features and Benefits**

- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Excellent Q<sub>gd</sub> x R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching Ensures More Reliability
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

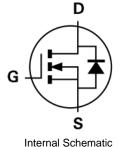




Notes:



**Bottom View** 



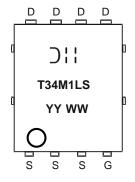
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT34M1LPS-13	PowerDI5060-8	2,500/Tape & Reel

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



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## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	30	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	21 17	Α
Continuous Drain Current, $V_{GS} = 10V$ (Note 7) $ T_C = +25^{\circ}C $ $ T_C = +70^{\circ}C $		I <sub>D</sub>	100 80	Α
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	3	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	250	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	I <sub>SM</sub>	250	Α	
Avalanche Current, L=0.1mH (Note 8)	I <sub>AS</sub>	38.5	Α	
Avalanche Energy, L=0.1mH (Note 8)	E <sub>AS</sub>	78	mJ	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	98	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	58	°C/W
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	P <sub>D</sub>	42	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	2.5	°C/W
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +150	°C

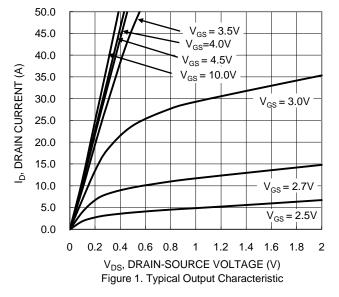
## Electrical Characteristics (T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{00} = 20V \ V_{00} = 0V$	
ON CHARACTERISTICS (Note 9)						•	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	J		2.6	3.2	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	_	3.7	5.2		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V$ , $I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	2242	_		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	960	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	217	_			
Gate Resistance	Rg	_	1.0	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	39	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	20	_	~C	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Qgs	_	5.6	_	nC	$V_{DD} = 15V, I_D = 20A$	
Gate-Drain Charge	Q <sub>gd</sub>		7.0	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	5.6	_			
Turn-On Rise Time	t <sub>R</sub>		13.8	_		$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		22.4	_	ns	$R_g = 3\Omega$ , $I_D = 20A$	
Turn-Off Fall Time	t <sub>F</sub>		11.4	_			
Reverse Recovery Time	t <sub>RR</sub>		22	_	ns	I <sub>F</sub> = 15A, dI/dt = 500A/μs	
Reverse Recovery Charge	$Q_{RR}$		27	_	nC	I <sub>F</sub> = 15A, dI/dt = 500A/μs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25$ °C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





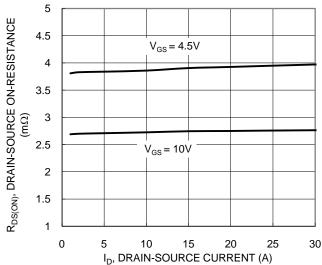


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

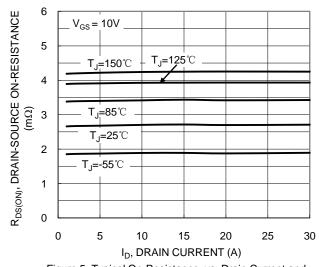
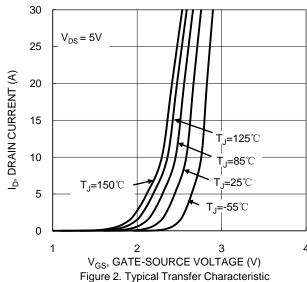


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



 $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE ( $m\Omega$ ) 50 45 40 35 30 25 20 15 10  $I_{D} = 20A$ 5 0 0 8 12 16 20 V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V)

Figure 4. Typical Transfer Characteristic

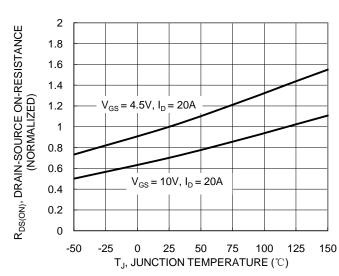


Figure 6. On-Resistance Variation with Junction Temperature

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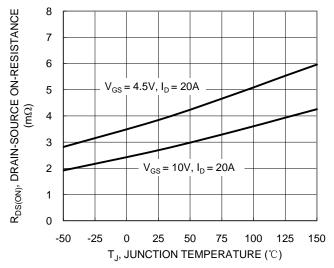


Figure 7. On-Resistance Variation with Junction Temperature

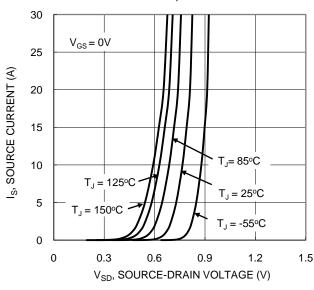
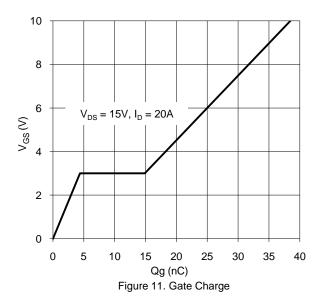


Figure 9. Diode Forward Voltage vs. Current



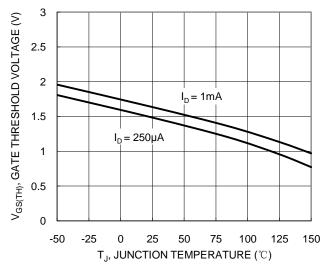


Figure 8. Gate Threshold Variation vs. Junction Temperature

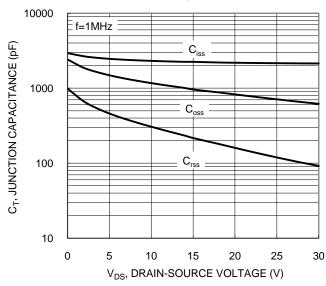
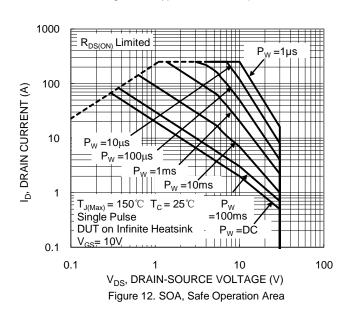


Figure 10. Typical Junction Capacitance



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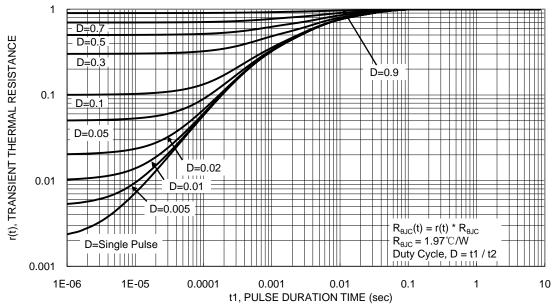


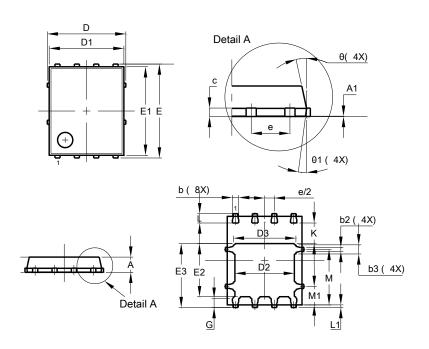
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

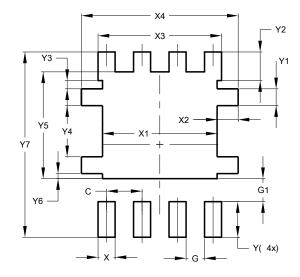


PowerDI5060-8						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
<b>A</b> 1	0.00 0.05 -					
b	0.33 0.51 0.4		0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D		5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90 4.30 4.10					
E	6.15 BSC					
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
M	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			

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